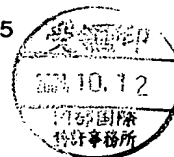


From the INTERNATIONAL BUREAU

**PCT**NOTIFICATION CONCERNING  
TRANSMITTAL OF COPY OF INTERNATIONAL  
APPLICATION AS PUBLISHED OR REPUBLISHED

To:

OKABE, Masao  
No. 602, Fuji Bldg.  
2-3, Marunouchi 3-chome  
Chiyoda-ku, Tokyo 1000005  
JAPON

Date of mailing (day/month/year)

07 October 2004 (07.10.2004)

Applicant's or agent's file reference

CFO17975WO

## IMPORTANT NOTICE

International application No.

PCT/JP2004/004072

International filing date (day/month/year)

24 March 2004 (24.03.2004)

Priority date (day/month/year)

26 March 2003 (26.03.2003)

Applicant

CANON KABUSHIKI KAISHA et al

The International Bureau transmits herewith the following documents:

copy of the international application as published by the International Bureau on 07 October 2004 (07.10.2004) under  
No. WO 2004/086516copy of international application as republished by the International Bureau on under  
No. WOFor an explanation as to the reason for this republication of the international application, reference is made to INID codes (15), (48)  
or (88) (as the case may be) on the front page of the attached document.The International Bureau of WIPO  
34, chemin des Colombettes  
1211 Geneva 20, Switzerland

Authorized officer

Masashi Honda

Facsimile No.+41 22 740 14 35

Facsimile No.+41 22 338 70 10

(19) World Intellectual Property  
Organization  
International Bureau



(43) International Publication Date  
7 October 2004 (07.10.2004)

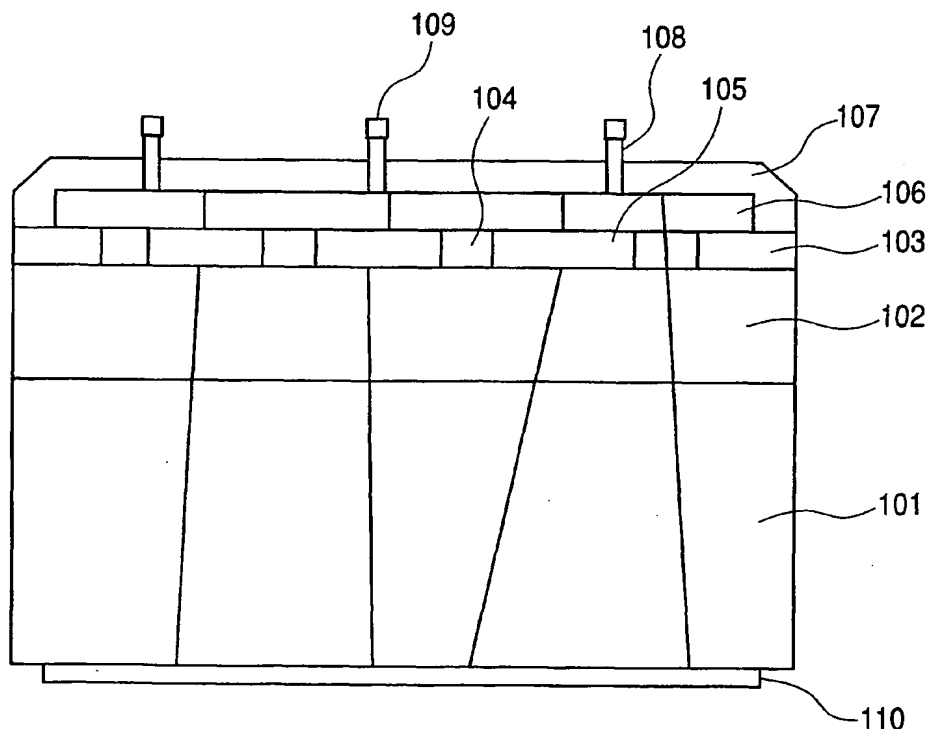
PCT

(10) International Publication Number  
**WO 2004/086516 A1**

- (51) International Patent Classification<sup>7</sup>: **H01L 31/06**
- (21) International Application Number:  
PCT/JP2004/004072
- (22) International Filing Date: 24 March 2004 (24.03.2004)
- (25) Filing Language: English
- (26) Publication Language: English
- (30) Priority Data:  
2003-084537 26 March 2003 (26.03.2003) JP
- (71) Applicant (for all designated States except US): **CANON KABUSHIKI KAISHA** [JP/JP]; 3-30-2, Shimomaruko, Ohta-ku, Tokyo 1468501 (JP).
- (72) Inventor; and
- (75) Inventor/Applicant (for US only): **ISHIHARA, Shunichi** [JP/JP]; c/o Canon Kabushiki Kaisha, 3-30-2, Shimomaruko, Ohta-ku, Tokyo 1468501 (JP).
- (74) Agents: **OKABE, Masao** et al.; No. 602, Fuji Bldg., 2-3, Marunouchi 3-chome, Chiyoda-ku, Tokyo 1000005 (JP).
- (81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

[Continued on next page]

(54) Title: SOLAR CELL



(57) Abstract: Provided is a solar cell having a silicon substrate for a solar cell, the substrate being formed by allowing a high-purity polycrystalline silicon layer to grow on a surface of a base that is sliced from a polycrystalline silicon ingot which is obtained by melting metal-grade silicon and solidifying the silicon in one direction, wherein a layer having a non-doped amorphous silicon phase and a microcrystalline silicon phase mixed together is stacked on the high-purity polycrystalline silicon layer.

WO 2004/086516 A1